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Iridium thin films deposited via pulsed laser deposition for future applications as transition-edge sensors

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Abstract

The University of Miami has recently started developing and studying high-resolution microcalorimeters operating near 100 mK for X-ray and particle physics and astrophysics. These detectors will be based on Transition Edge Sensors technology fabricated using iridium thin films deposited via the Pulsed Laser Deposition technique. We report here the preliminary result of the room temperature characterization of the Ir thin films, and an overview of future plans to use the films as transition edge sensors.

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Keywords: Pulsed laser deposition; Transition edge sensors; Iridium

1. Introduction

Iridium has a transition temperature of 112 mK, suitable for many Transition Edge Sensors (TES) applications. However, the iridium melting point of 2719 K precludes many of the more conventional deposition techniques. Iridium films and iridium/gold bilayers have been deposited with e-beam evaporation [1] and iridium deposited using RF magnetron sputtering techniques is also being investigated for TES X-ray calorimeters [2]. However, iridium films deposited using Pulsed Laser Deposition (PLD) have not been investigated. PLD films are expected to be of higher purity and have better adhesion [3]. In iridium thin films, the transition temperature is a property of the material and does not depend on relative thickness between layers or on the quality of an interface layer. For this reason, when compared to bilayer TES devices, the proposed relatively simple, single layer devices have the potential to drastically improve both the reproducibility of the transition temperature between fabrication runs and the uniformity of the detectors when building arrays.

There is some evidence that iridium films may have poorer thermal conductivity than bilayers [2]. A careful investigation of the thermal properties of Ir thin films and the appropriate detector engineering will therefore be necessary for best performance.

2. PLD

The PLD facility at the University of Miami consists of a Lambda Physik's COMPex 200 Kr-F excimer laser, that operates at a wavelength of 248 nm (UV), and a high vacuum chamber that is

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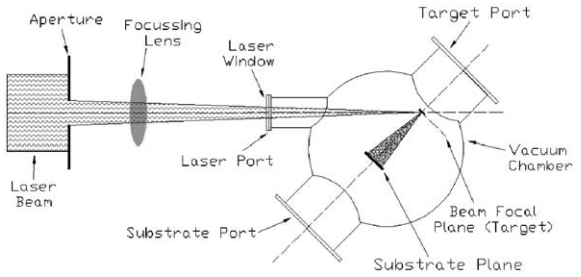

Fig. 1. Schematic top view of the PLD system at the University of Miami.

capable of reaching a pressure below 10^{-6} Torr. Fig. 1 shows a schematic of the system and illustrates the relative orientations of the laser beam, vacuum chamber, target and substrate. The UV laser beam exits the laser aperture, travels through air and is focused with a lens before it enters the vacuum chamber. The laser hits the iridium target at an angle of about 45° to the target's normal. At the point of impact the laser is focused to generate intensities of about 10^9 W/cm^2 necessary for the evaporation of Ir. The laser pulse width is 12 ns and the repetition rate is 10 Hz. The iridium target is typically a few cm in diameter and a few mm thick. Components not shown in the figure are a substrate heater and a target rotation stage that enables uniform ablation. The substrates were optically polished Si(1 0 0) wafers, cleaned ultrasonically in acetone and alcohol. The target–substrate distance was 4 mm.

3. PLD versus other techniques

Pulsed laser deposition (PLD) has been used to deposit thin metal films since the 1960s [4]. The use of PLD for depositing more complex substances, such as high T_c superconductors, has grown significantly in the last decades, while more conventional sputtering/evaporation techniques are now often used to deposit high quality metal films—with a few exceptions. One of these exceptions is iridium whose high melting point (2719 K) precludes many of the more conventional techniques. A variety of techniques including PLD [5], radio-frequency (RF) magnetron sputtering [2], and electron-beam evaporation [1] have recently been used to deposit thin films of iridium. However, El Khakani et al. find that the PLD process produces higher quality films than the RF sputtering process [3] and points out that the PLD process leads to higher purity films with enhanced adhesion. Each of these qualities is of paramount importance for TES applications: the detrimental effects of ferromagnetic impurities were apparent in Nagel et al. [1], who used e-beam evaporation, while Fukuda et al. [2] (who used RF sputtering) had to increase the substrate to a fairly high temperature of 900 K in order to increase the adhesion between the substrate and the Ir film. El Khakani et al. [3] found that PLD yields good adhesion at lower temperature, and zero-stress levels in Ir films deposited at 400°C on both bare and amorphous SiC:H-coated Si(1 0 0) substrates. As pointed out in Chrisey and Hubler [6] the high quality of PLD films is believed to result from the energetic ablated species together with the supersaturated vapor flux.

4. Film crystalline structure

Scanning Electron Microscopy (SEM) was used to examine the morphology of Ir films deposited via PLD with substrate temperatures of 300°C, 500°C, and 700°C. Films deposited at 300°C and 500°C have a polycrystalline structure with average grain size in the order of tens of nm (see Fig. 2), in agreement with what was previously observed by El Khakani et al. [5]. As part of their characterization of Ir films deposited via PLD, El Khakani et al. [2] found that the films have a polycrystalline structure with average grain size changing from 10 to 20 nm when the substrate temperature was changed from 20°C to 600°C.

The film deposited at 700°C shows a very different behavior, with an average grain size of several hundred nm (see Fig. 3). This seems to indicate the presence of a substrate critical temperature, T_C between 600°C and 700°C at which the grain size is drastically enhanced. We plan to use low temperature resistance measurements and X-ray diffraction technique to determine the best structure for TES applications.

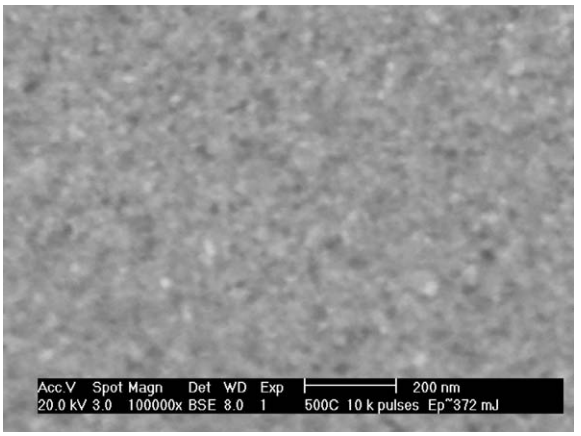

Fig. 2. SEM image of an Ir thin film deposited at a substrate temperature of 500°C.

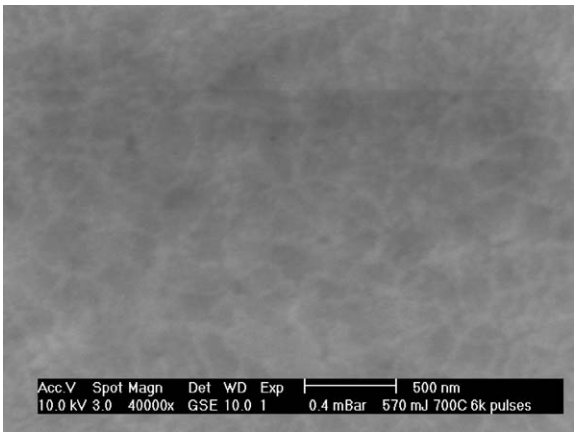

Fig. 3. SEM image of an Ir thin film deposited at a substrate temperature of 700°C.

5. Deposition of particulates

One of the problems often associated with PLD is the emission of particles a few microns in diameter from the target. In our system we empirically observed that most large particles are emitted at large angles, outside the substrate area. SEM indicates a particle density of 1–2 particles per mm^2, a level that is not expected to affect the performance of our TES.

6. From Ir thin films to Ir TES

The main goal of our effort is the fabrication of transition-edge sensors for X-ray and γ-ray detectors. For high energy γ-ray single-pixel detectors we simply plan to use Ir thin films deposited on silicon and suspended through Al wires bonded directly to the film.

For lower energy, X-ray detectors, the goal is to manufacture arrays with about 1000 detectors and single pixel size of the order of 200 μm. Iridium is difficult to etch, but there are a few promising directions that we plan to investigate. The first one is the use of a wet etch electro-chemical technique [7]. Recent results are promising, and we successfully built sub-mm-size structures. The fabrication of smaller size structures is currently being pursued. A second possibility is the use of a lift-off technique. Because PLD heats the substrate, a classical lift-off technique using photo-resist is not viable, but the use of Al as lift-off layer seems promising [8].

We plan to use Al deposited via thermal evaporation or sputtering for the electrical connections and wet etching for the silicon. To suspend the devices, we plan to test both silicon nitride and silicon carbide membranes.

Acknowledgements

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